

SPECIFICATION

DEVICE NAME : IGBT

TYPE NAME : 1MBH10D-060

SPEC. No. :

DATE :

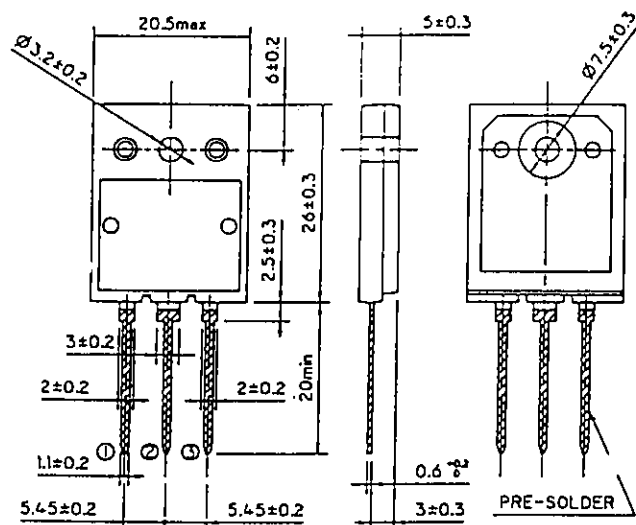
Fuji Electric Co.,Ltd.

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	DATE	NAME	APPROVED		Fuji Electric Co.,Ltd.		
DRAWN					DWG.NO.	1/12	
CHECKED							

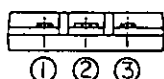
1MBH10D-060

1. Outline Drawing

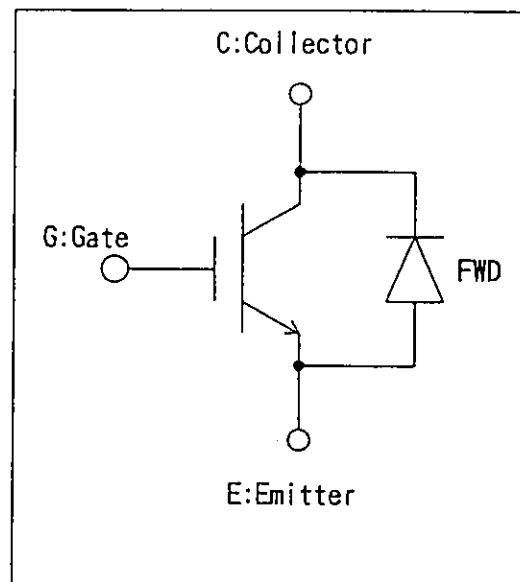


CONNECTION

- ① GATE
② COLLECTOR
③ EMITTER



2. Equivalent circuit



3. Absolute maximum ratings (Tc=25°C)

Items			Symbols	Ratings	Units
Collector-Emitter Voltage			V_{CES}	600	V
Gate-Emitter Voltage			V_{GES}	± 20	V
Collector Current	DC	Tc=25 °C	I_{C25}	30	A
		Tc=115°C	I_{C115}	10	A
	1ms	Tc=25 °C	I_{cp}	80	A
IGBT Max. Power Dissipation			P_c	115	W
FWD Max. Power Dissipation			P_c	55	W
Operating Temperature			T_j	+ 150	°C
Storage Temperature			T_{stg}	-40 ~ +150	°C
Mounting Screw Torque			—	70	N · cm

4. Electrical Characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

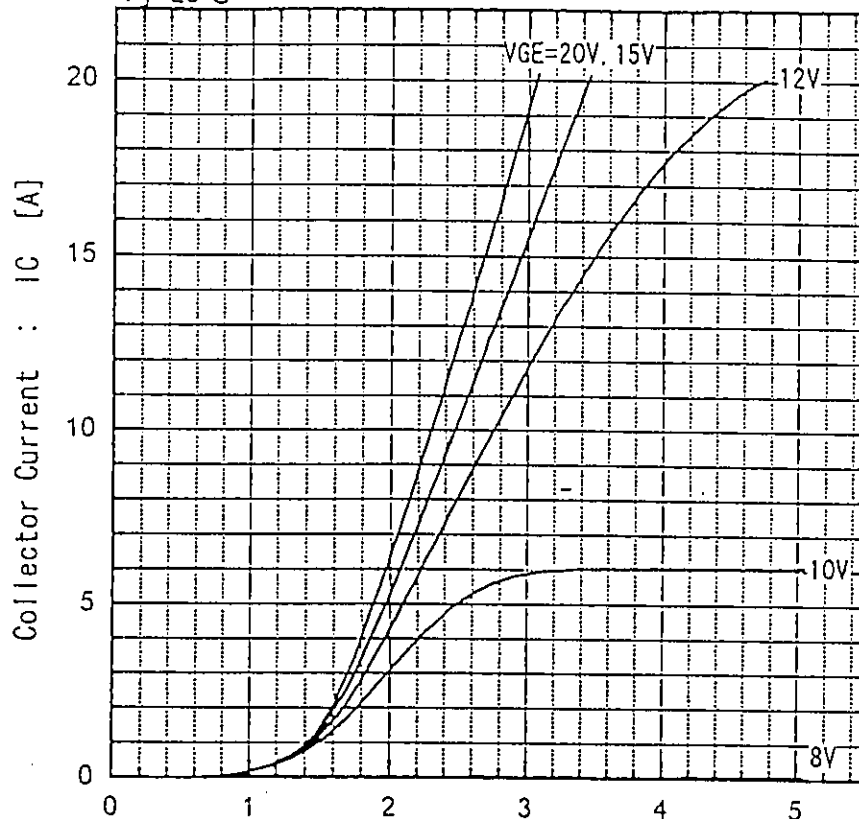
Items		Symbols	Characteristics			Conditions	Unit
			min.	typ.	max.		
Zero gate voltage Collector Current		I_{CES}			1.0	$V_{GE} = 0V$ $V_{CE} = 600V$	mA
Gate-Emitter leakage Current		I_{GES}			20	$V_{CE} = 0V$ $V_{GE} = \pm 20V$	μA
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	5.5		8.5	$V_{CE} = 20V$ $I_C = 10mA$	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			3.0	$V_{GE} = 15V$ $I_C = 10A$	V
Input capacitance		C_{ies}		700		$V_{GE} = 0V$	pF
Output capacitance		C_{oes}		150		$V_{CE} = 10V$	
Reverse transfer capacitance		C_{res}		20		$f = 1MHz$	
Switching Time	Turn-on time	t_{on}			1.2	$V_{CC} = 300V$ $I_C = 10A$ $V_{GE} = \pm 15V$ $R_G = 220\Omega$ (Half Bridge)	μs
		t_r			0.6		
	Turn-off time	t_{off}			1.0		
		t_f			0.35		
	Turn-on time	t_{on}		0.16		$V_{CC} = 300V$ $I_C = 10A$ $V_{GE} = +15V$ $R_G = 22\Omega$ (Half Bridge)	
		t_r		0.11			
	Turn-off time	t_{off}		0.30			
		t_f			0.35		
FWD forward voltage drop		V_F			3.0	$I_F = 10A$	V
Reverse recovery time		t_{rr}			0.3	$I_F=10A, V_{GE}=-10V$ $V_R= 200V$ $di/dt=100A/\mu s$	μs

5. Thermal resistance characteristics

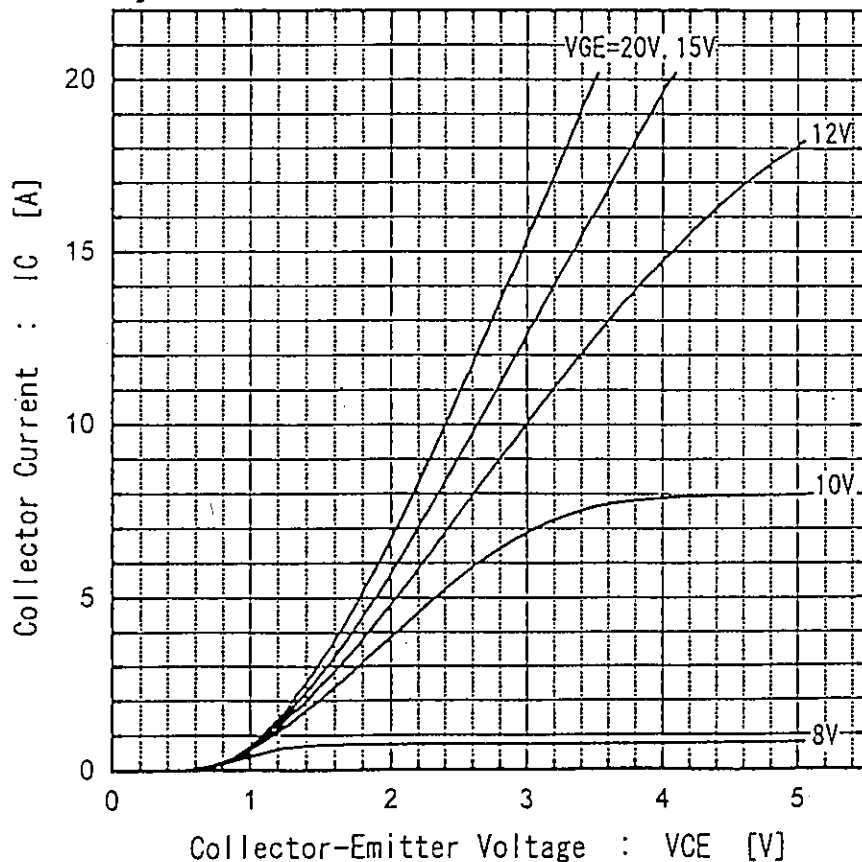
Items		Symbols	Characteristics			Conditions	Unit
			min.	typ.	max.		
Thermal resistance		$R_{th(j-c)}$			1.08	IGBT	$^{\circ}\text{C/W}$
		$R_{th(j-c)}$			2.27	FWD	

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Collector Current vs. Collector-Emitter Voltage
 $T_j = 25^\circ\text{C}$



Collector Current vs. Collector-Emitter Voltage
 $T_j = 125^\circ\text{C}$



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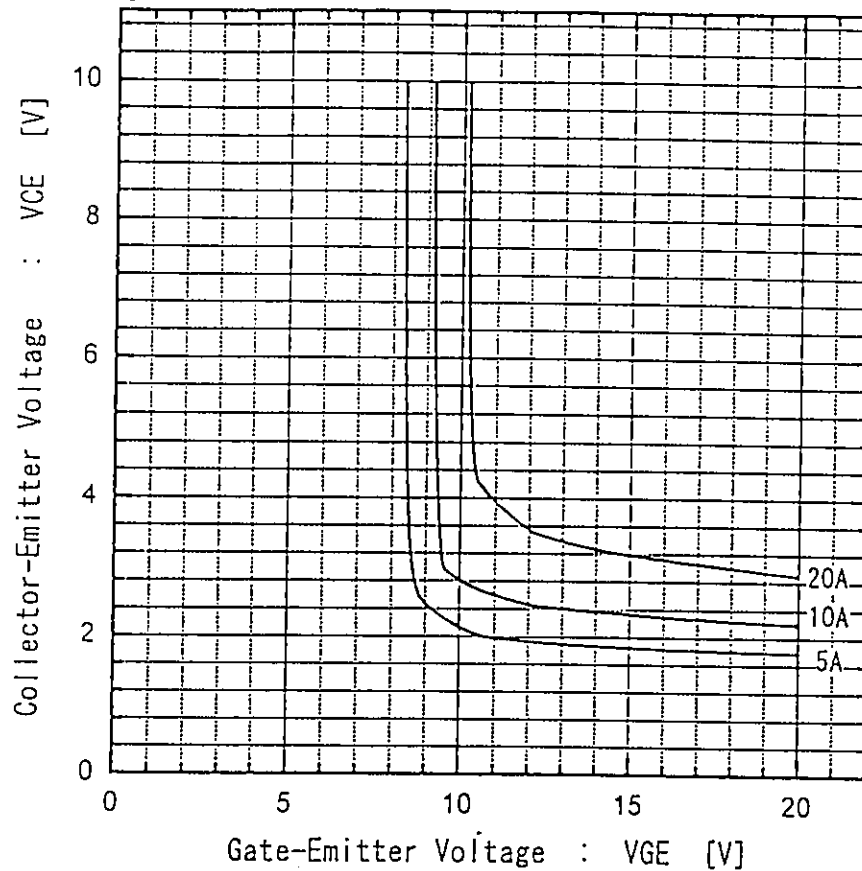
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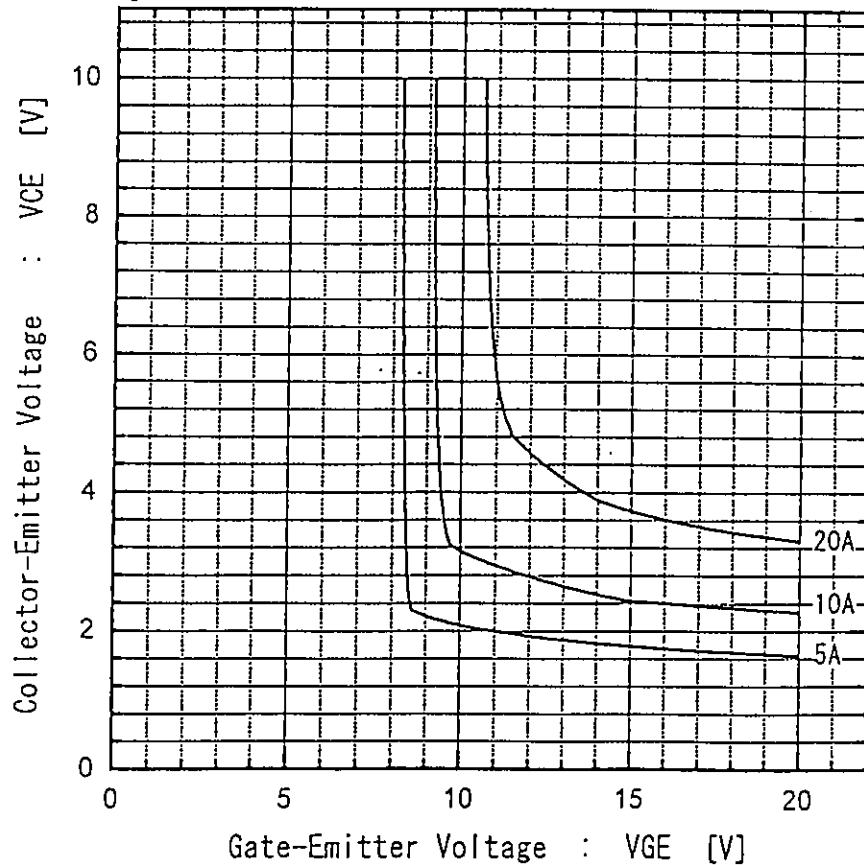
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Collector-Emitter Voltage vs Gate-Emitter Voltage
T_j=25°C



Collector-Emitter Voltage vs Gate-Emitter Voltage
T_j=125°C



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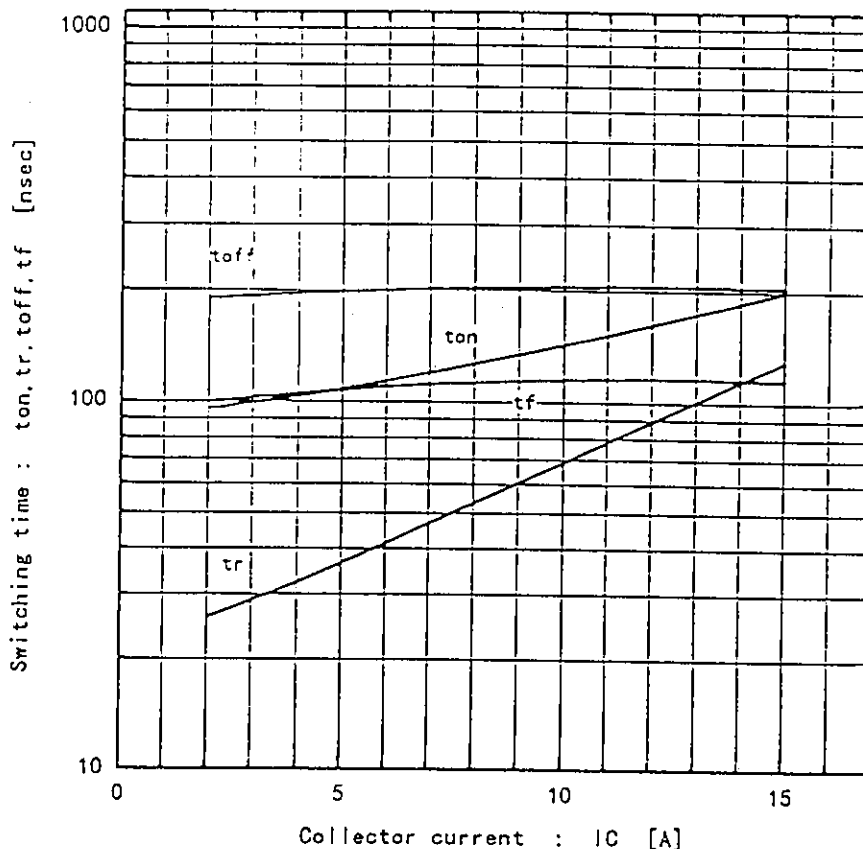
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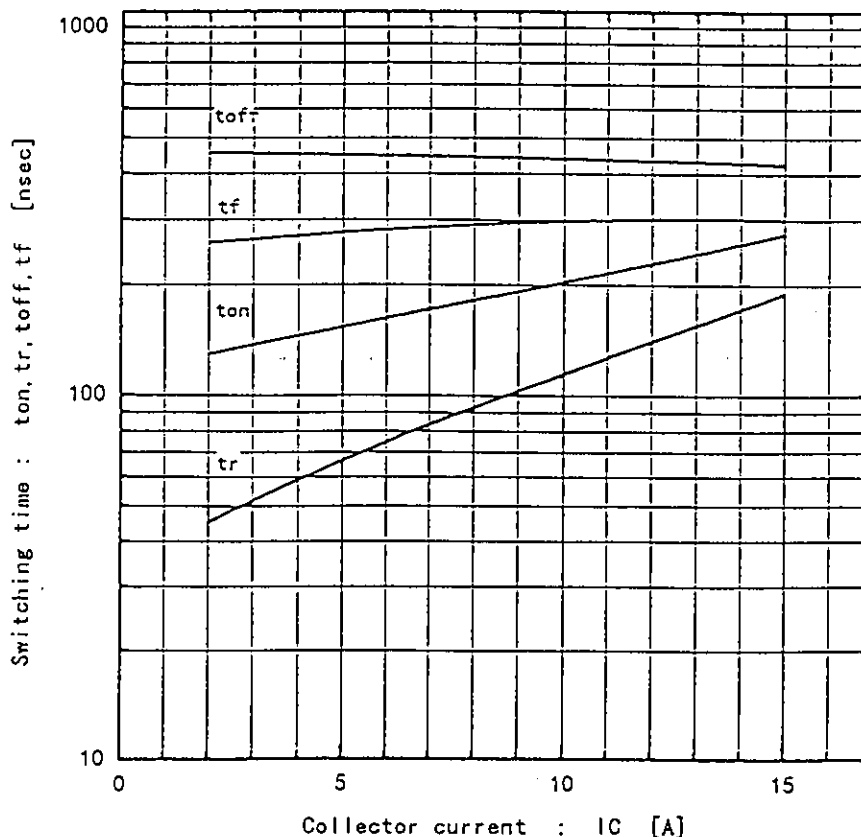
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Switching time vs. Collector current
 $V_{CC}=300V$, $R_G=22\Omega$, $V_{GE}=\pm 15V$, $T_j=25^\circ C$

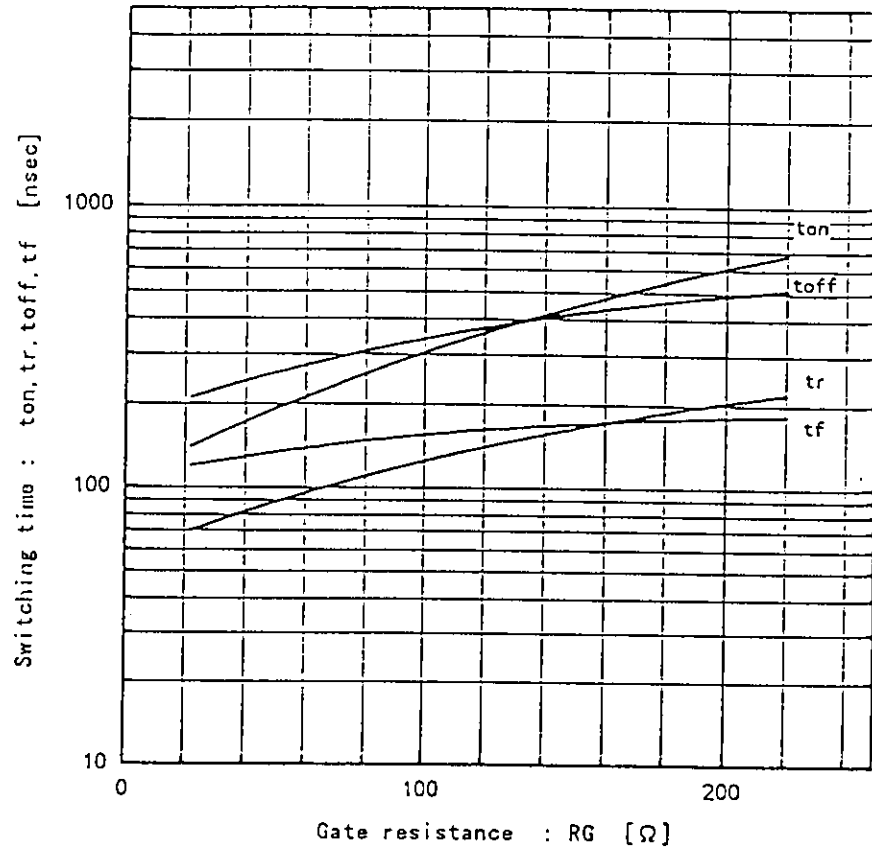


Switching time vs. Collector current
 $V_{CC}=300V$, $R_G=22\Omega$, $V_{GE}=\pm 15V$, $T_j=125^\circ C$

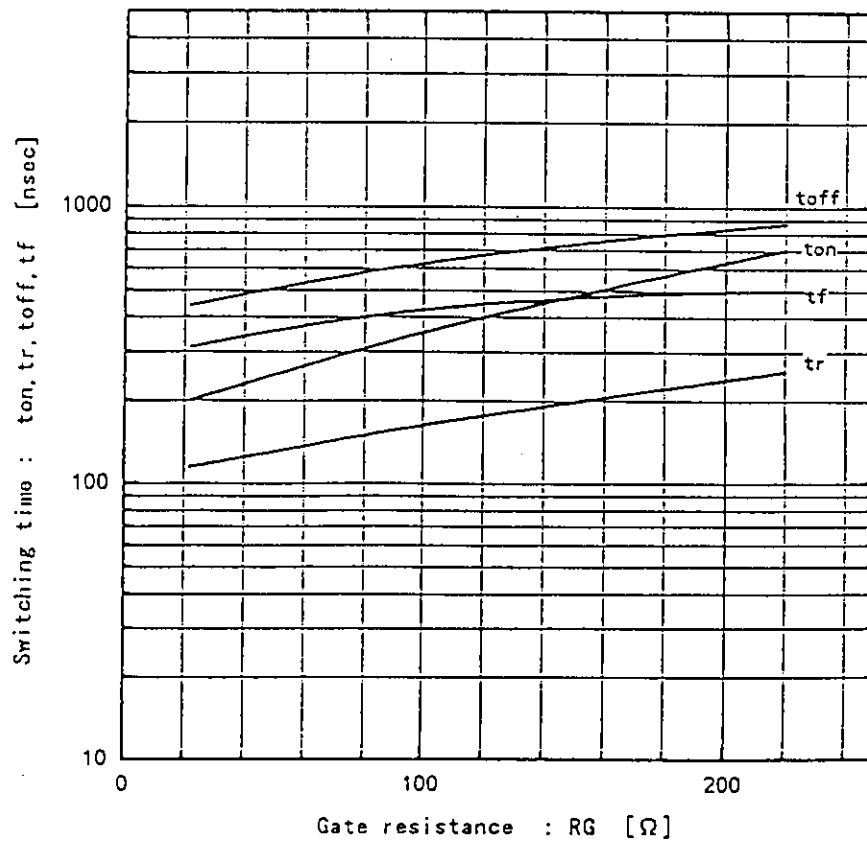


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Switching time vs. R_G
 $V_{CC}=300V$, $I_C=10A$, $V_{GE}=\pm 15V$, $T_j=25^\circ C$



Switching time vs. R_G
 $V_{CC}=300V$, $I_C=10A$, $V_{GE}=\pm 15V$, $T_j=125^\circ C$



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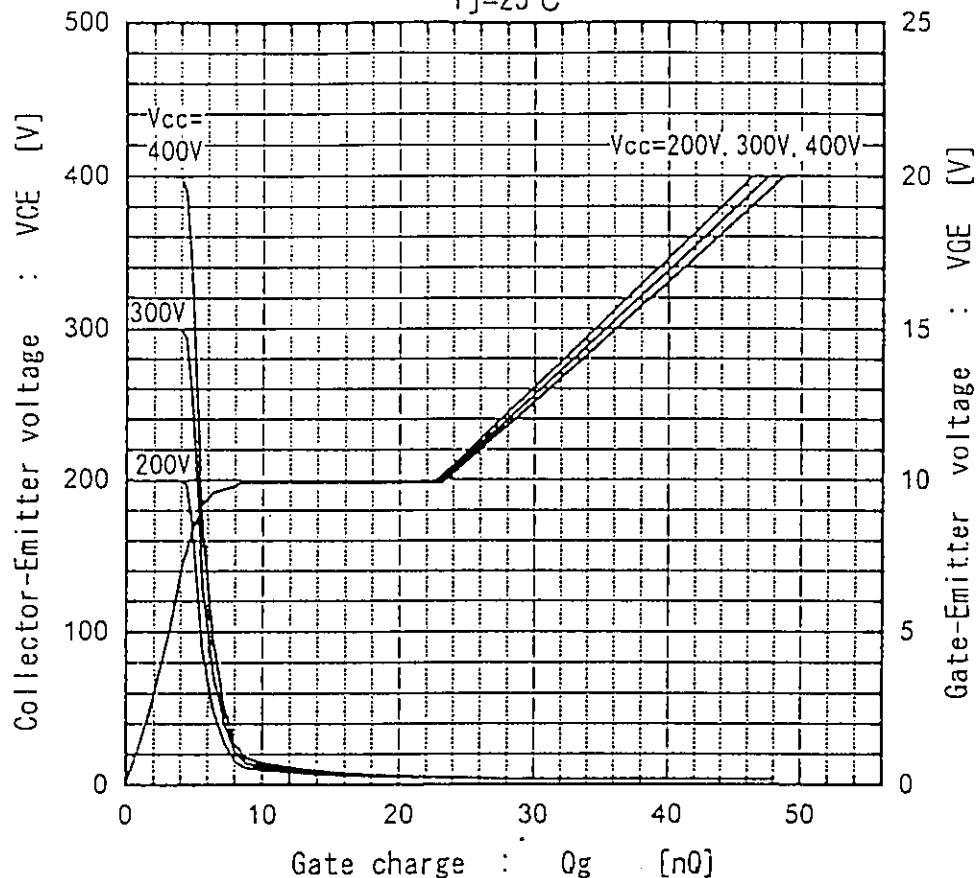
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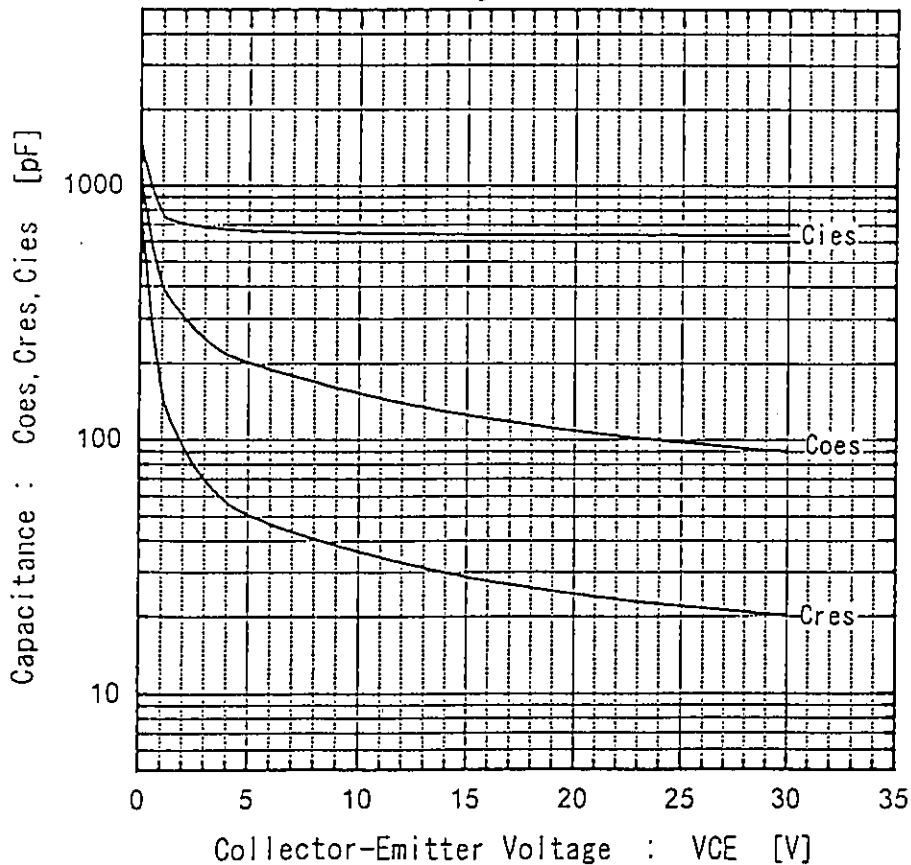
Dynamic input characteristics

$T_j = 25^\circ\text{C}$



Capacitance vs. Collector-Emitter voltage

$T_j = 25^\circ\text{C}$



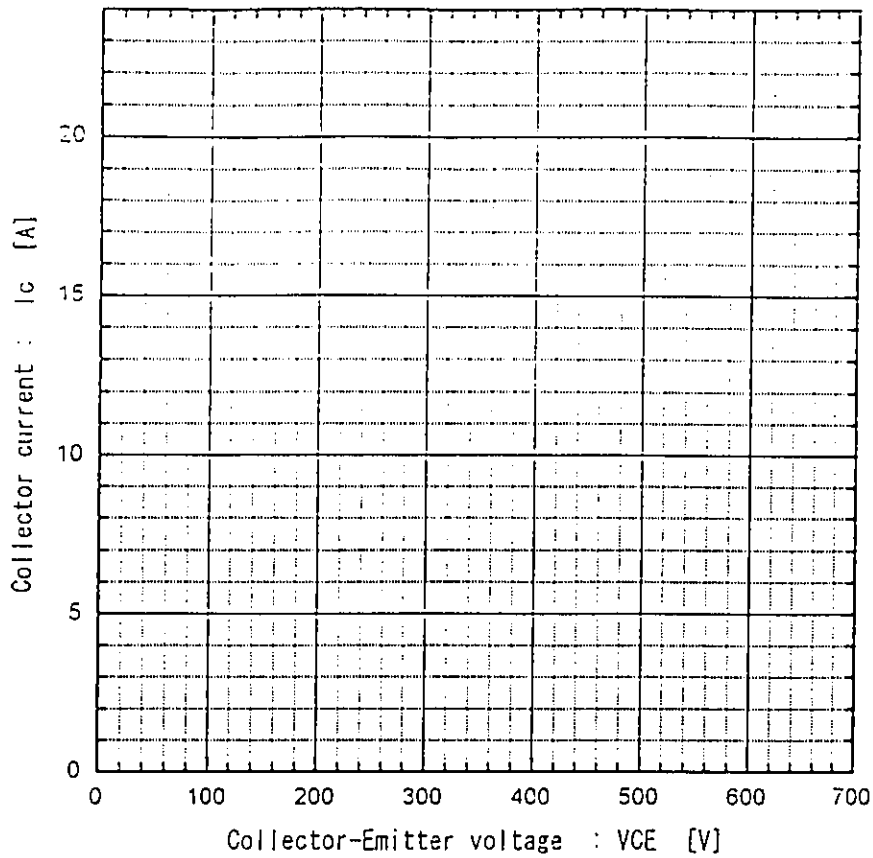
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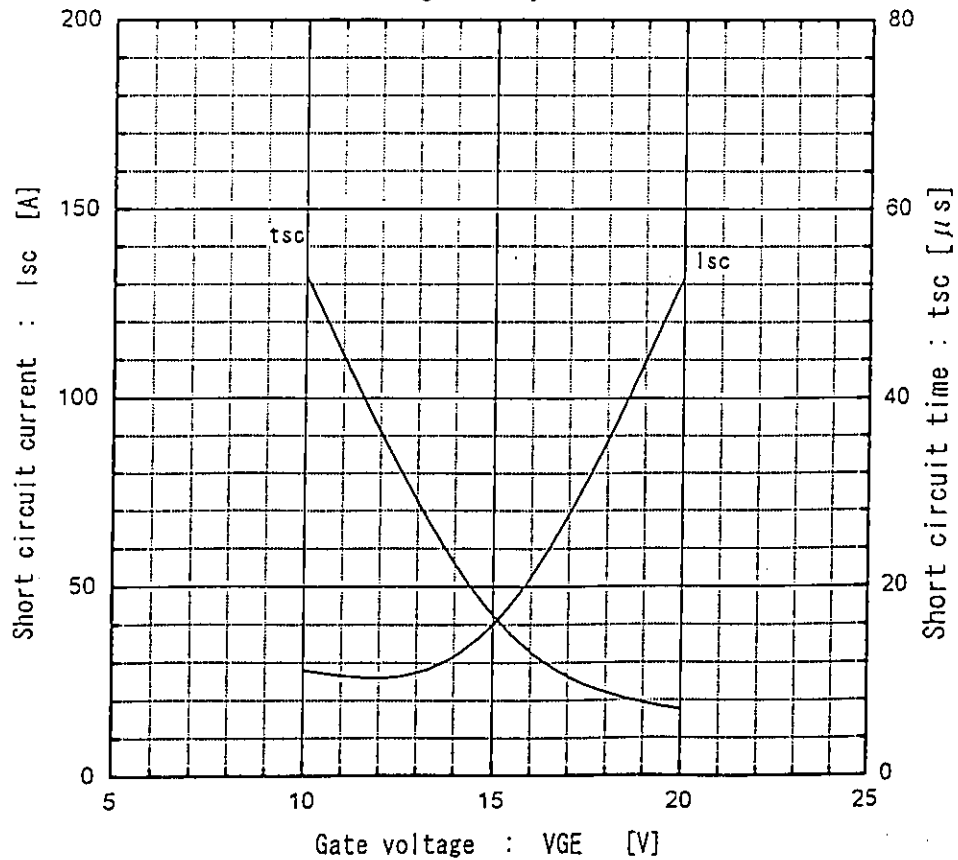
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Reverse Biased Safe Operating Area
 $+V_{GE}=15V$, $-V_{GE}\leq 15V$, $T_j\leq 125^\circ C$, $R_g\geq 22\Omega$



Typical short circuit capability
 $V_{CC}=400V$, $R_g=22\Omega$, $T_j=125^\circ C$



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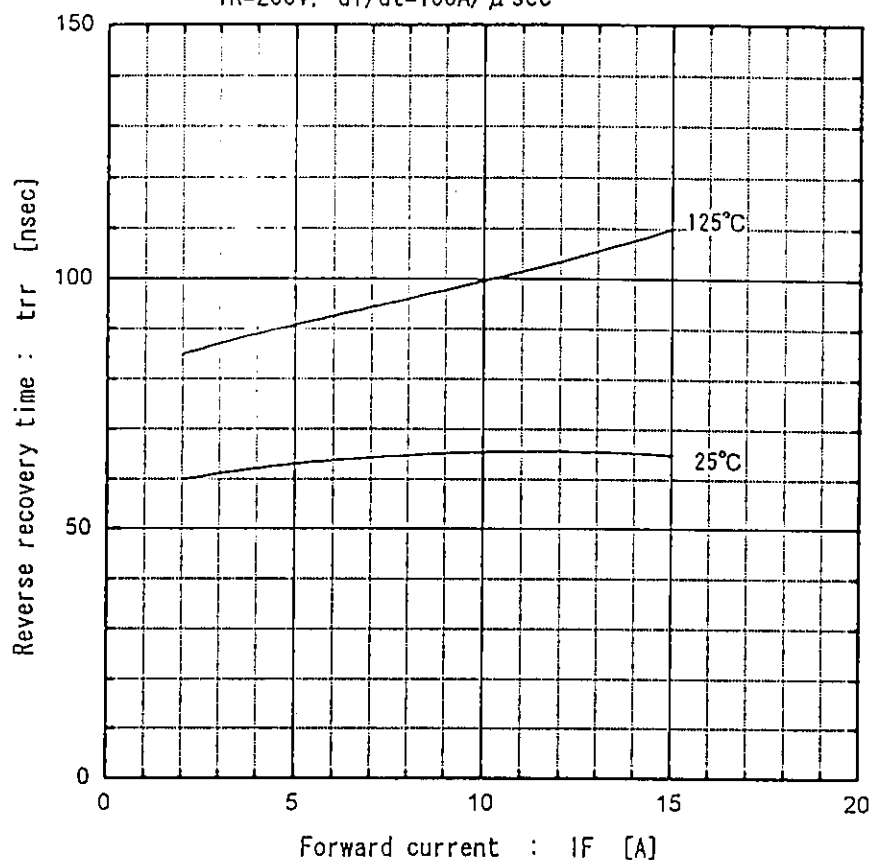
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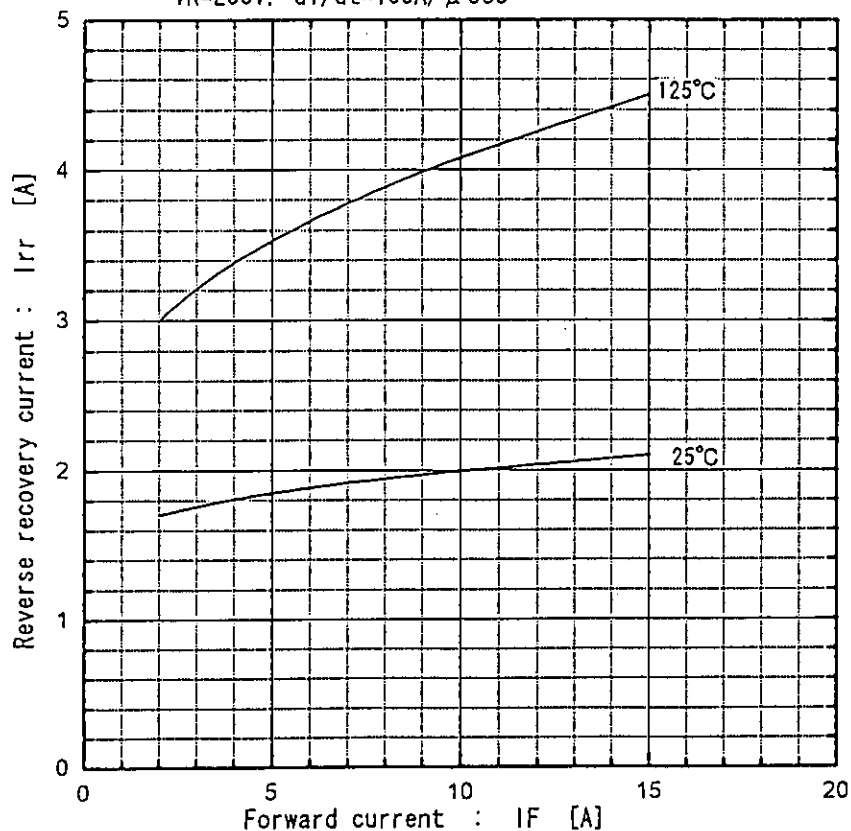
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Reverse recovery time vs. Forward current
VR=200V, $-di/dt=100A/\mu\text{sec}$



Reverse recovery current vs. Forward current
VR=200V, $-di/dt=100A/\mu\text{sec}$



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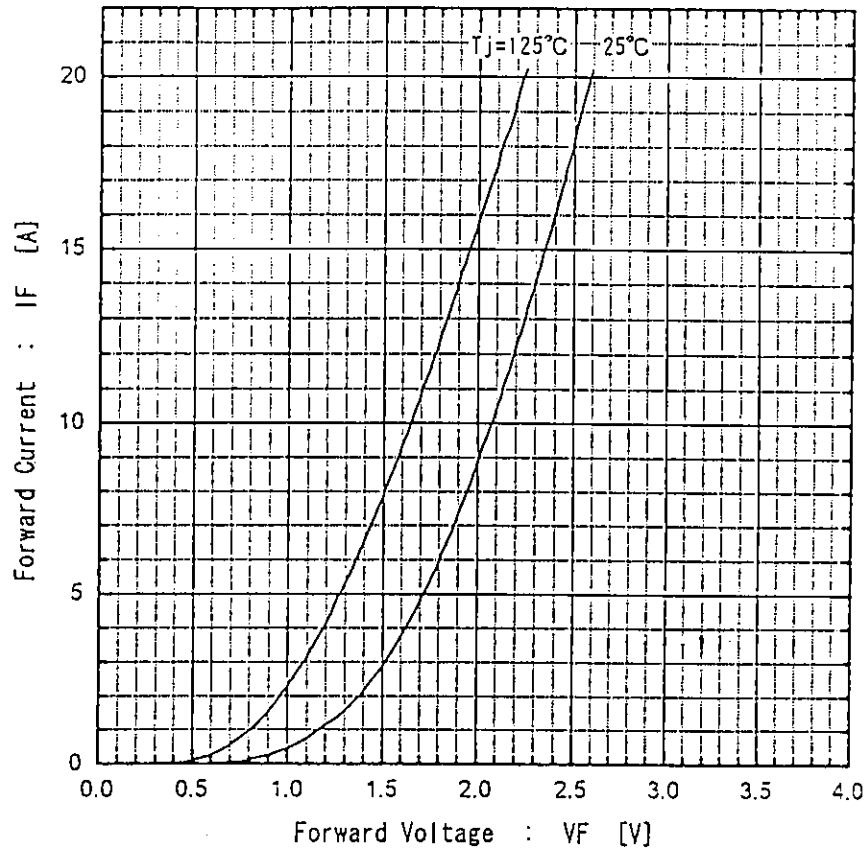
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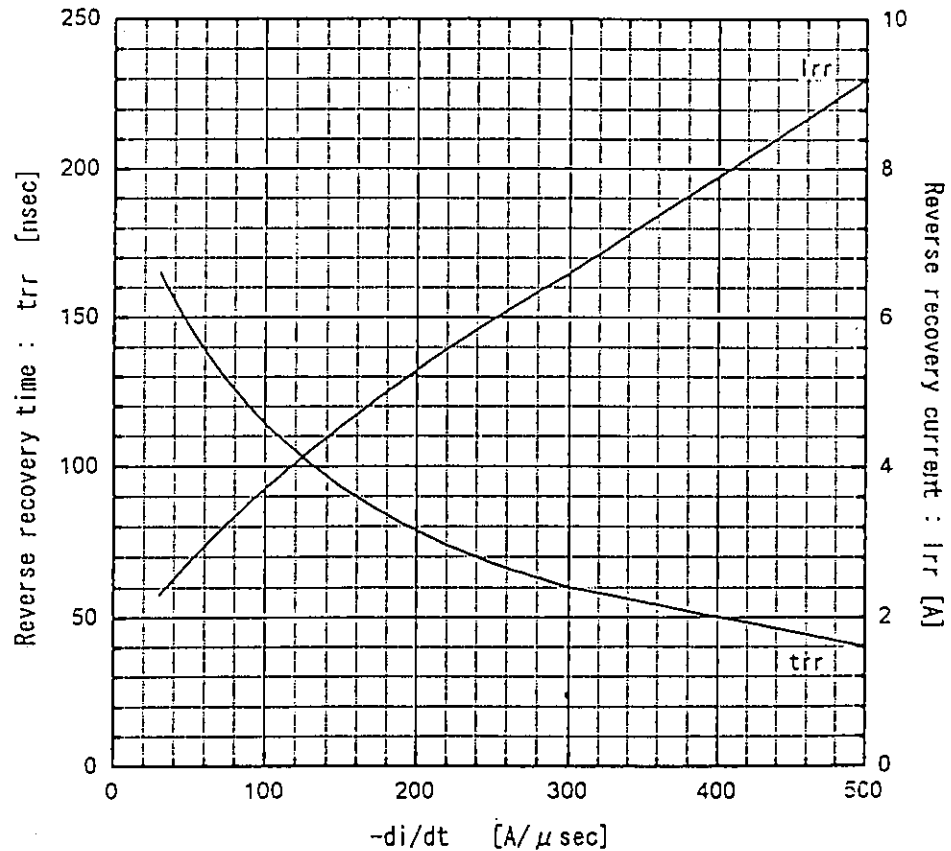
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Forward voltage vs. Forward current



Reverse recovery characteristics vs. $-di/dt$
 $I_F = 10\text{A}$, $T_j = 125^\circ\text{C}$



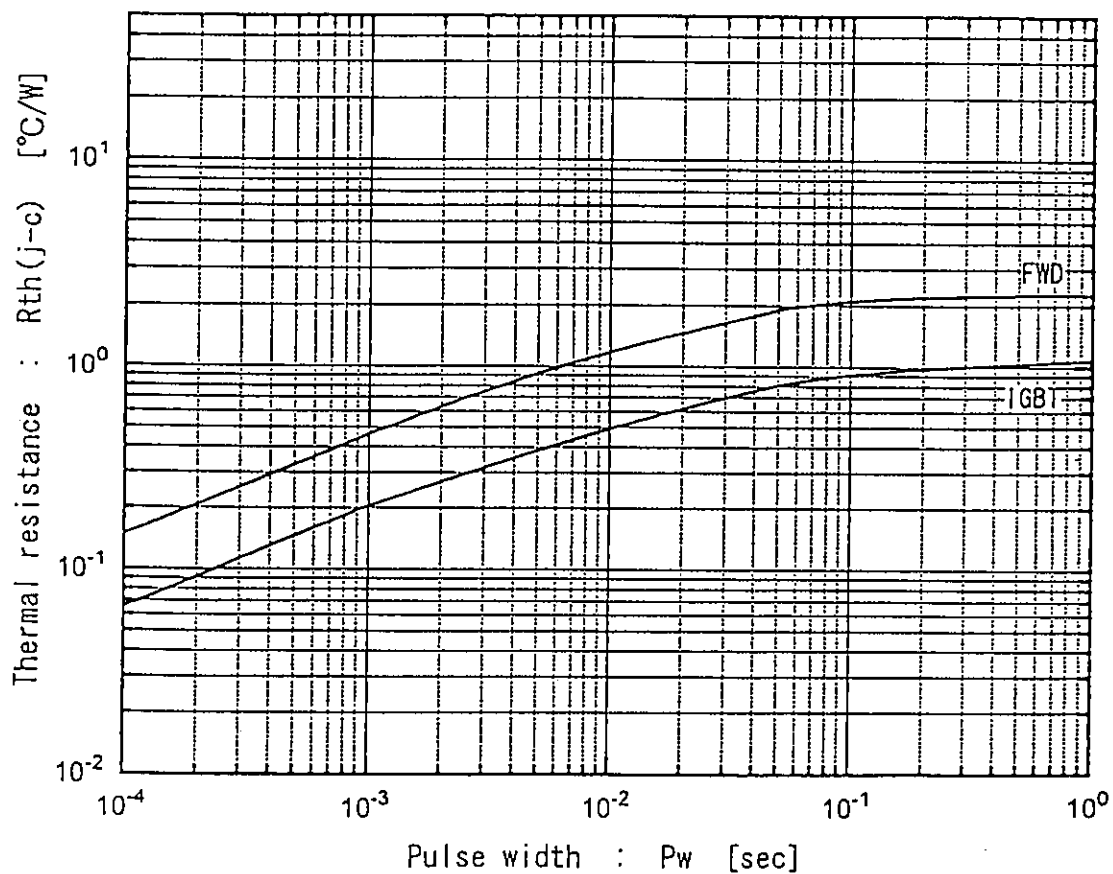
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Transient thermal resistance



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